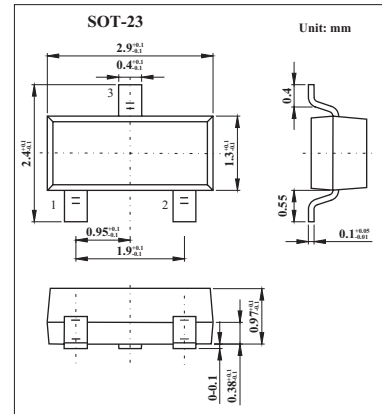
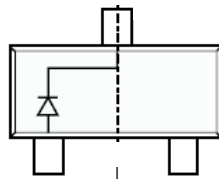


KAT750(BAT750)

■ Features

- Very Low Forward Voltage Drop
- High Conductance
- For Use in DC-DC Converter, PCMCIA, and Mobile Telecommunications Applications



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Peak repetitive reverse voltage	V _{RRM}	40	V
Working peak reverse voltage	V _{RWM}		
DC blocking voltage	V _R		
RMS reverse voltage	V _{R(RMS)}	28	V
Average rectified output current	I _O	0.75	A
Non-Repetitive Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	5.5	A
Power dissipation	P _D	350	mW
Typical Thermal Resistance Junction to Ambient	R _{θJA}	286	°C/W
Operating and storage temperature range	T _j , T _{stg}	-40 to +125	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Reverse Breakdown Voltage	V _{(BR)R}	I _R = 300 μA	40	45		V
Forward voltage	V _F	I _F = 50mA		225	280	mV
		I _F = 100mA		235	310	
		I _F = 250mA		290	350	
		I _F = 500mA		340	420	
		I _F = 750mA		390	490	
		I _F = 1000mA		420	540	
Leakage current	I _R	V _R = 15V		50	100	μA
Junction Capacitance	C _J	V _R = 0, f = 1.0MHz		175		pF
		V _R = 25V, f = 1.0MHz		25		

■ Marking

Marking	K77 or K79
---------	------------